

IN THE CLAIMS:

Please cancel claims 1-13, 16 and 17 without prejudice to or disclaimer of the subject matter recited therein.

Please amend claims 14, 15, 18 and 19 as follows:

LISTING OF CURRENT CLAIMS

Claims 1-13. (Canceled)

Claim 14. (Currently Amended) A power rectifier device, comprising:

an n+ substrate having a n-drift formed thereon;

a cathode metal layer formed on a surface of said n+ substrate opposite said n-drift layer;

5 an active region having a metal silicide layer formed thereon;

a termination region being defined at positions outer of said active region;
region and having termination trenches formed therein;

an insulating layer formed on said n-drift layer and on said termination region;

10 four ~~first~~ trenches along a line and filled with an un-doped polycrystalline silicon layer spaced from each other and ~~the a~~ second and ~~the a~~ third of said trenches formed into said n- drift layer of said substrate, and ~~the a~~ first and ~~the a~~ fourth of said trenches formed into said insulating layer and said n- drift layer of said substrate;

15 said active region being defined from a first interval to a second interval, wherein said first interval is in between the first one and the second one of said ~~first~~ trenches, and said second interval is in between the third one and the fourth one of said ~~first~~ trenches;

a thermal oxide layer formed on said termination region;

20 an anode electrode formed on said metal silicide layer and extended to cover the first and the fourth of said ~~first trenches~~ trenches, wherein said insulating layer is a stack layer, from said epi-layer sequentially, formed of a first oxide layer, a nitride layer, and a second oxide layer having a thickness between 5nm to 100nm, 50nm to 300nm, and 0nm to 1000nm, respectively.

Claim 15. (Currently Amended) The power rectifier device according to Claim 14 wherein said active region further comprises the first and the fourth of said trenches, so that said insulating layer formed thereon is removed and thus said metal silicide layer is formed over said four ~~first~~ trenches and said anode electrode is formed extended to cover a portion of said termination trenches.

Claim 16. (Canceled)

Claim 17. (Canceled)

Claim 18. (Currently Amended) The power rectifier device according to Claim 14 further comprises an oxide lining formed on a sidewall and bottom of said four ~~first~~ trenches and said termination trenches.

Claim 19. (Currently Amended) The power rectifier device according to Claim 6 14 wherein said anode electrode is a layer selected from Al, AlCu, AlSiCu or a stack layer formed of Ti, Ni, and Ag.